

## isc N-Channel MOSFET Transistor

2SK3617D

## FEATURES

- Drain Current :  $I_D = 6A @ T_C = 25^\circ C$
- Drain Source Voltage  
:  $V_{DSS} = 100V(\text{Min})$
- Static Drain-Source On-Resistance  
:  $R_{DS(on)} = 225m\Omega (\text{Max}) @ V_{GS} = 10V$
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

## DESCRIPTION

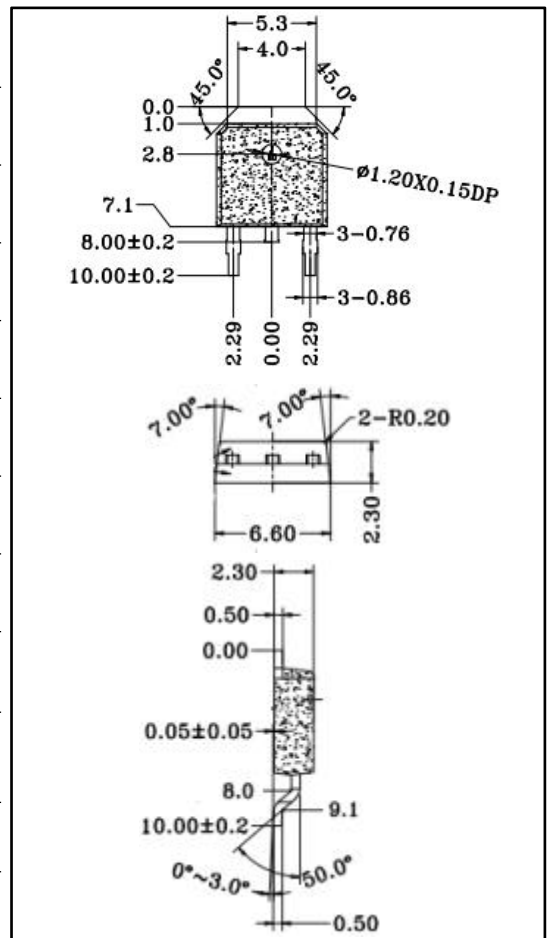
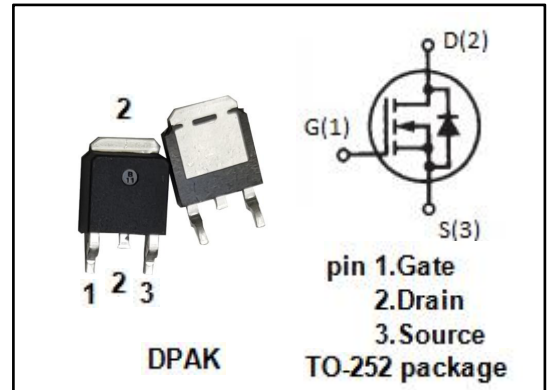
- motor drive, DC-DC converter, power switch and solenoid drive.

ABSOLUTE MAXIMUM RATINGS( $T_a = 25^\circ C$ )

| SYMBOL    | PARAMETER                              | VALUE    | UNIT       |
|-----------|--|----------|------------|
| $V_{DSS}$ | Drain-Source Voltage                   | 100      | V          |
| $V_{GS}$  | Gate-Source Voltage-Continuous         | $\pm 20$ | V          |
| $I_D$     | Drain Current-Continuous               | 6        | A          |
| $I_{DM}$  | Drain Current-Single Pulse             | 24       | A          |
| $P_D$     | Total Dissipation @ $T_C = 25^\circ C$ | 15       | W          |
| $T_J$     | Max. Operating Junction Temperature    | -55~150  | $^\circ C$ |
| $T_{stg}$ | Storage Temperature                    | -55~150  | $^\circ C$ |

## THERMAL CHARACTERISTICS

| SYMBOL       | PARAMETER                            | MAX  | UNIT         |
|--------------|--------------------------------------|------|--------------|
| $R_{th j-c}$ | Thermal Resistance, Junction to Case | 8.33 | $^\circ C/W$ |



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## ELECTRICAL CHARACTERISTICS

 $T_c=25^{\circ}\text{C}$  unless otherwise specified

| SYMBOL        | PARAMETER                       | CONDITIONS                             | MIN | MAX      | UNIT             |
|---------------|---------------------------------|--|-----|----------|------------------|
| $V_{(BR)DSS}$ | Drain-Source Breakdown Voltage  | $V_{GS}=0$ ; $I_D=1\text{mA}$          | 100 | --       | V                |
| $V_{GS(th)}$  | Gate Threshold Voltage          | $V_{DS}=10\text{V}$ ; $I_D=1\text{mA}$ | 1.2 | 2.6      | V                |
| $R_{DS(on)1}$ | Drain-Source On-Resistance      | $V_{GS}=10\text{V}$ ; $I_D=3\text{A}$  | --  | 225      | $\text{m}\Omega$ |
| $R_{DS(on)2}$ | Drain-Source On-Resistance      | $V_{GS}=4\text{V}$ ; $I_D=3\text{A}$   | --  | 315      | $\text{m}\Omega$ |
| $I_{GSS}$     | Gate-Body Leakage Current       | $V_{GS}=\pm 16\text{V}$ ; $V_{DS}=0$   | --  | $\pm 10$ | $\mu\text{A}$    |
| $I_{DSS}$     | Zero Gate Voltage Drain Current | $V_{DS}=100\text{V}$ ; $V_{GS}=0$      | --  | 1        | $\mu\text{A}$    |
| $V_{SD}$      | Forward On-Voltage              | $I_S=6\text{A}$ ; $V_{GS}=0$           | --  | 1.2      | V                |

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